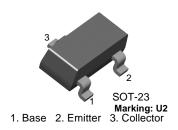


# BCX20

## **NPN Epitaxial Silicon Transistor**

## **Switching and Amplifier Applications**



## Absolute Maximum Ratings $T_a = 25$ °C unless otherwise noted

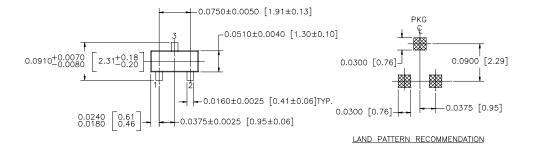
Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	25	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current (DC)	800	Α
P <sub>C</sub>	Collector Dissipation	310	W
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-65 ~ 150	°C

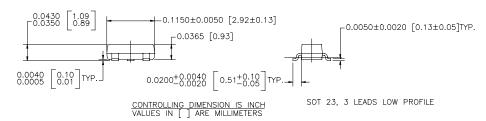
## **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max	Units
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	25		V
BV <sub>CES</sub>	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu A, V_{BE} = 0$	30		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	5		V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CE</sub> = 20V, V <sub>BE</sub> = 0		100	nA
I <sub>EBO</sub>	Emitter-Base Cut-off Current	$V_{BE} = 5V, I_{C} = 0$		10	nA
h <sub>FE1</sub> h <sub>FE2</sub> h <sub>FE3</sub>	DC Current Gain	$V_{CE} = 1V, I_{C} = 100mA$ $V_{CE} = 1V, I_{C} = 300mA$ $V_{CE} = 1V, I_{C} = 500mA$	100 70 40	600	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$		0.62	V
V <sub>BE(on)</sub>	Base-Emitter Saturation Voltage	V <sub>CE</sub> = 1A, I <sub>B</sub> = 500mA		1.2	V

### **Mechanical Dimensions**

# SOT-23





NOTE : UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

Dimensions in Millimeters

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CROSSVOLT™	GlobalOptoisolator™	MicroFET™	PowerTrench®	SuperSOT™-6
DOME™	GTO™ .	MicroPak™	QFET®	SuperSOT™-8
EcoSPARK™	HiSeC™	MICROWIRE™	QS™	SyncFET™
E <sup>2</sup> CMOS <sup>TM</sup>	I <sup>2</sup> C <sup>TM</sup>	MSX <sup>TM</sup>	QT Optoelectronics™	TinyLogic <sup>®</sup>
EnSigna™	i-Lo™	MSXPro™	Quiet Series™	TINYOPTO™
FACT™	ImpliedDisconnect™	$OCX^{TM}$	RapidConfigure™	TruTranslation™
FACT Quiet Series <sup>™</sup>		OCXPro™	RapidConnect™	UHC™
Across the board. Around the world.™		OPTOLOGIC®	μSerDes™	UltraFET <sup>®</sup>
The Power Fran		OPTOPLANAR™	SILENT SWITCHER®	UniFET™
Programmable Active Droop™		PACMAN™	SMART START™	VCX <sup>TM</sup>

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#### **Definition of Terms**

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